

### ABSTRACT OF THE DISCLOSURE

A susceptor structure capable of discharging the atmosphere containing dopant species and filling a wafer pocket, without causing a large quantity of a raw material gas to flow from the front surface side of a susceptor to under the susceptor. The susceptor having an approximately round disk shape and having a concave wafer pocket on the front surface thereof for accommodating a wafer, comprises a gas inlet notch passing through from a side surface or a rear surface of the susceptor to the wafer pocket, and a gas discharge notch passing through from the wafer pocket to the side surface or the rear surface of the susceptor. A carrier gas is introduced from the gas inlet notch of the susceptor into the wafer pocket, as shown by arrow b and the gas present inside the wafer pocket is discharged from the gas discharge notch, as shown by arrow c, by using the rotation of the susceptor during epitaxial film growth.